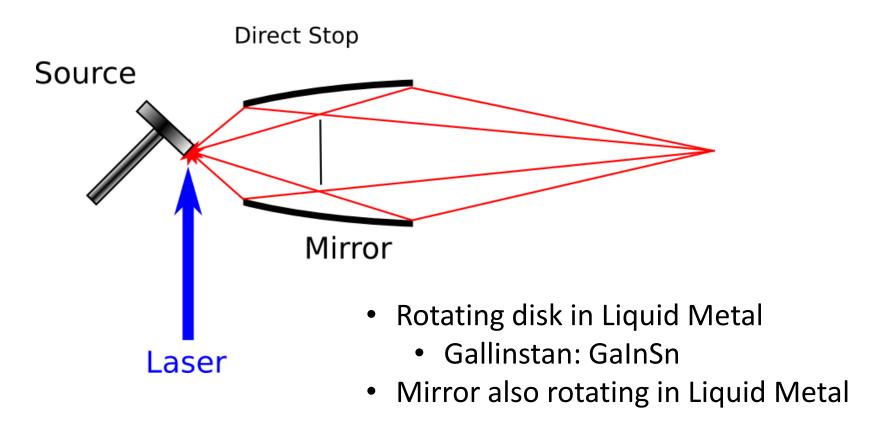


TUNABLE, HIGH BRIGHTNESS LAB-SCALE SOFT X-RAY PHOTONS

<u>Paul Sheridan</u>, Fergal O Reilly, Padraig Dunne, Emma Sokell and Kenneth Fahy

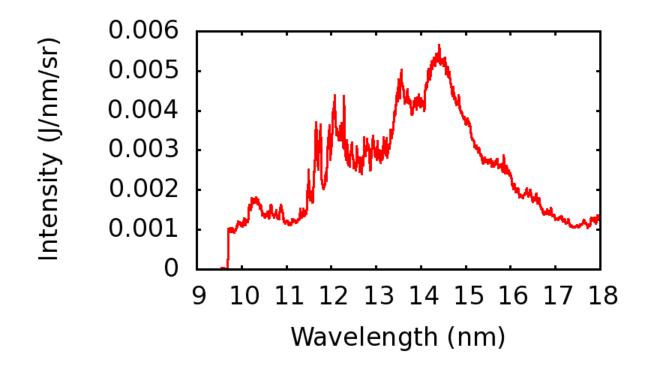


Source Concept



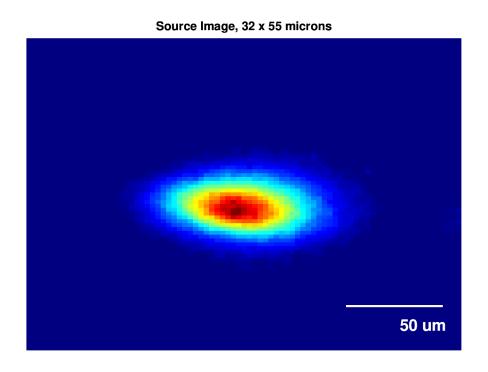
Characterisation

Spectroscopy, ¼ m absolutely calibrated



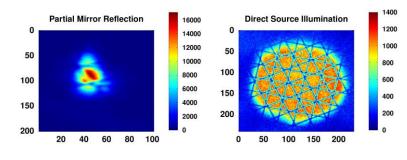
Characterisation

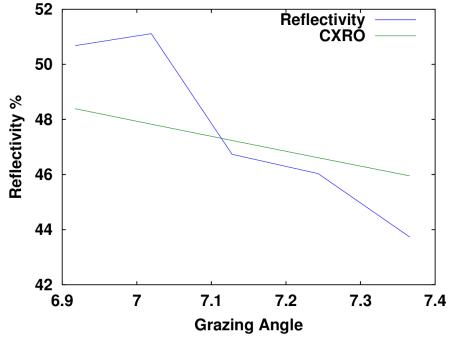
- Multilayer (Mo/Si) mirrors
 - Concave
 - Flat
- Zirconium filter
- Imaged at 45 degrees



Characterisation

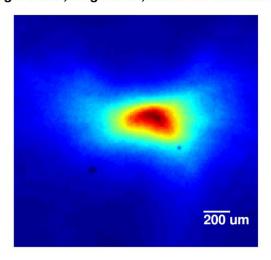
- Mirror Reflectivity
- Measured in-situ



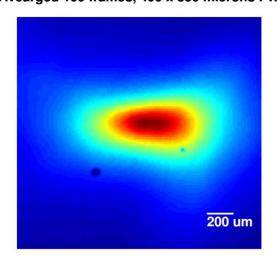


Intermediate Focus

IF: Single frame, single shot, 300 x 600 microns FWHM



IF: Avearged 100 frames, 400 x 850 microns FWHM

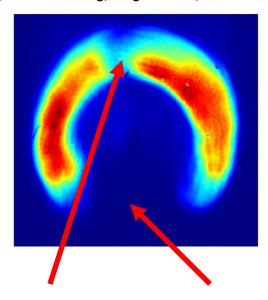


Collector Mirror has a 10x magnification

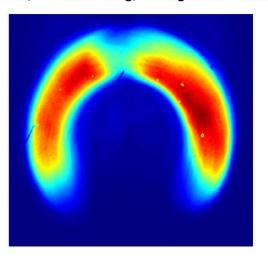
Extra Focal Ring

Camera 60 mm extra focal

STAN, Extrafocal Ring, Single Frame, 200 Shots/Frame



STAN, Extrafocal Ring, Averaged 50 Frames



Direct Stop Mount

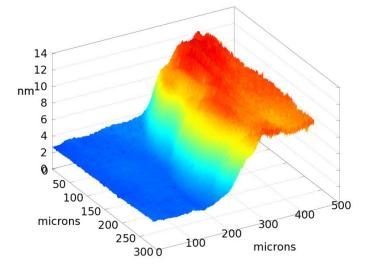
Collector partially submerged in liquid bath.

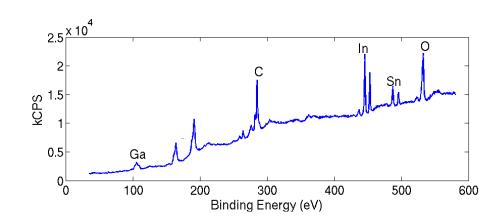
IF Debris Results

- Slide before IF capillary
- <2 nm of metal/hour
- No particulates
- XPS compositional analysis
 - 60% C
 - 26% O
 - 14% Liquid Metal

Improvements:

- Increase vacuum level, currently
 1e-6 mbar
- Use gas backflow at IF capillary

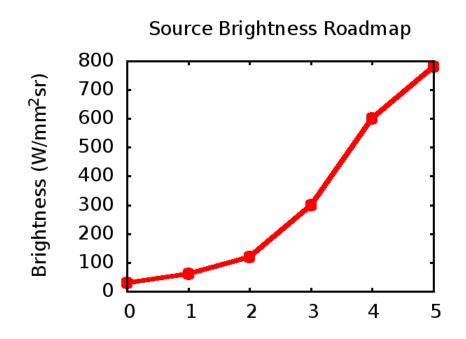




Brightness

- Current Brightness: 30 W/mm²sr
- Clear path to 780 W/mm²sr

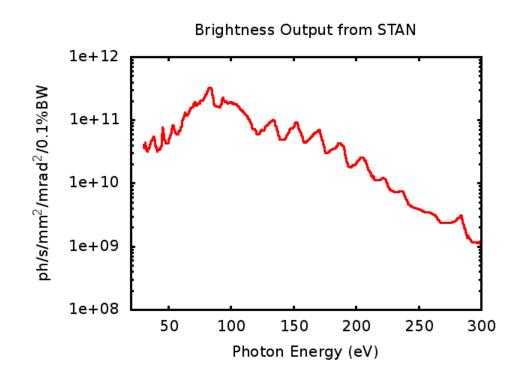
 Total laser input required 200 W current 55 W



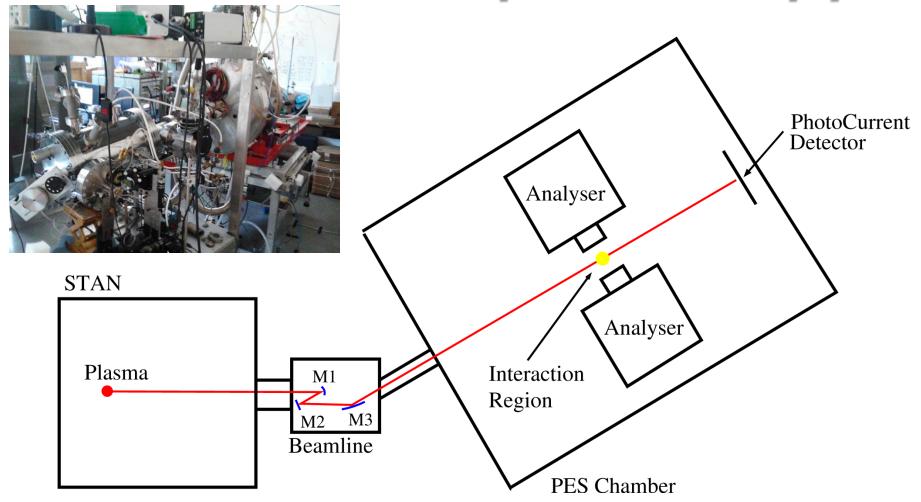
Applications

STAN

- Broadband output
- Ideal for photoelectron spectroscopy
- In-house PES chamber

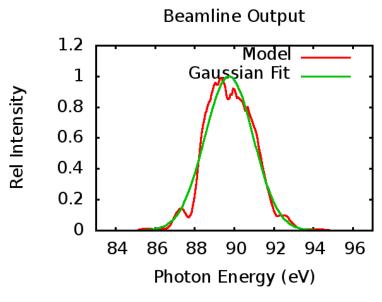


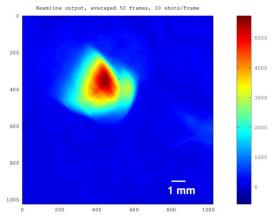
PhotoElectron Spectroscopy



PES Beamline

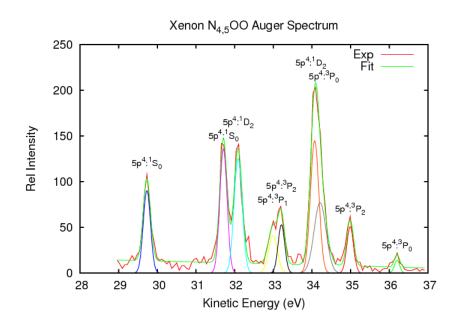
- Multilayer mirrors
 - 1 Concave (f=125mm)
 - 1 flat
- Spectral Narrowing
- 89 eV
- 3 eV FWHM
- Focused to < 3 x 3 mm²





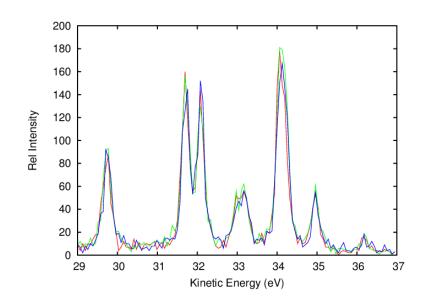
PES Experiment

- Xenon N_{4,5}OO Auger
 Decay
- Acquisition time 23 minutes



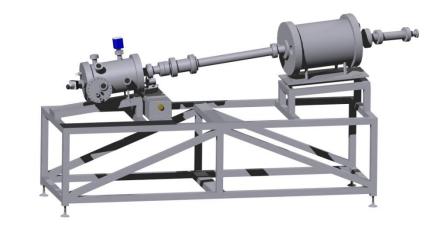
PES Experiment

- Xenon N_{4,5}OO Auger
 Decay
- Acquisition time 23 minutes
- High Stability
 - Repeated 3 timesover 4 hours.
 - No variation

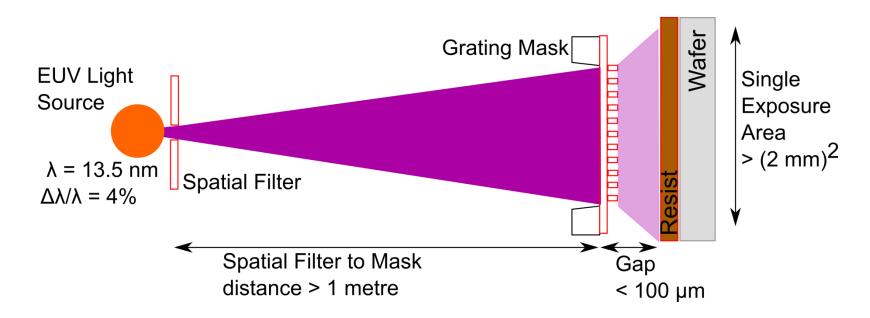


Ongoing Work

- Building Custom Monochromator
 - PGM Design
 - -10 100 eV
 - Resolving Power: >300 to >1200
 - Designed for STAN
- Different designs
 for broader energy range



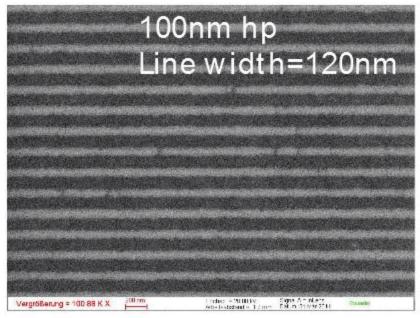
EUV Interference Lithography



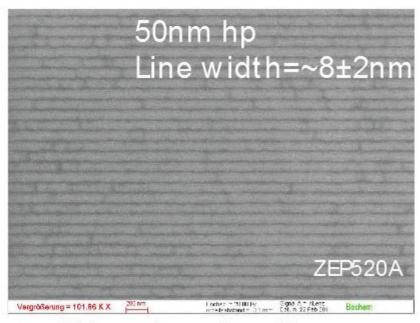
Talbot Self Imaging

- Periodic Arrays
- HP equal to half the grating period

EUV Interference Lithography



Distance to mask z few µm Proximity printing



Distance to mask z= 50 µm achromatic Talbot (with the same transmission mask!)

Serhiy Danylyuk - COST Action MP0601 Talk 2012

Other STAN Applications

Photo Emission Electron Microscopy (PEEM)

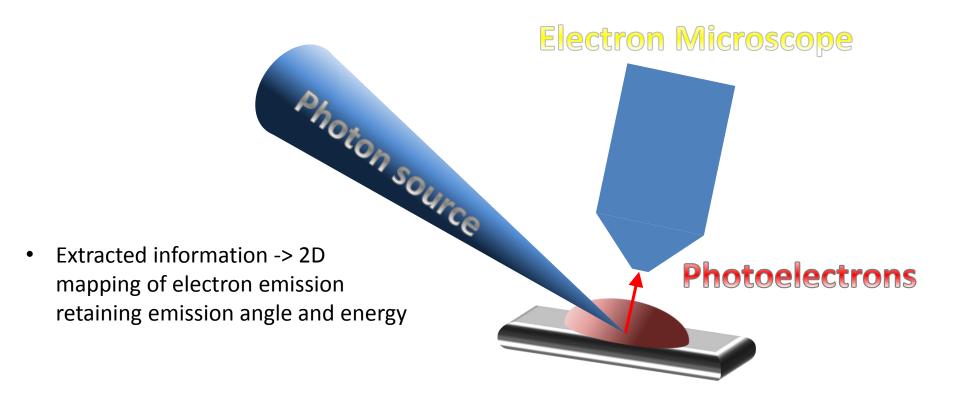


Image: Elmitec 2013

PEEM

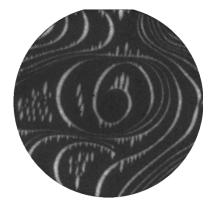
Cu Layer on Mo(110)surface



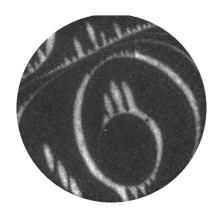




Field of view 20µm



Field of view 10µm



Field of view 5µm

Light sources currently used

- UV Lamps
- Synchrotrons



Image: Elmitec 2013

Conclusions

- The STAN light source is a simple and elegant high brightness EUV source
- Well characterised
- Running routinely in the lab
- Can be applied to multiple applications
 - PES, XPS
 - PEEM
 - Interference Lithography

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Acknowledgements









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We would like to acknowledge the kind support of Regina Soufli, Lawrence Livermore National Laboratory,
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and the technical workshop, UCD School of Physics

Thank you for listening